

RESPONSE TO FINAL OFFICE ACTION
S/N 10/666,317
Page 2 of 10

IN THE CLAIMS

1. (Previously Presented) A method for controlling dimensions of structures formed on a substrate using an etch process, comprising:
 - providing the substrate having a patterned etch mask formed thereon;
 - measuring dimensions of elements of the mask on the substrate;
 - adjusting a process recipe for an overetch step of the etch process using results of measuring the dimensions; and
 - forming structures on the substrate by performing the etch process that uses the adjusted process recipe.
2. (Original) The method of claim 1 wherein the substrate is a semiconductor wafer.
3. (Original) The method of claim 1 wherein the mask is a patterned hard etch mask or a patterned photoresist mask.
4. (Original) The method of claim 1 wherein the structures are formed in at least one material layer disposed beneath the mask.
5. (Original) The method of claim 1 wherein the dimensions are smallest widths of the elements.
6. (Original) The method of claim 1 wherein the dimensions are measured using a non-destructive measuring technique.
7. (Original) The method of claim 6 wherein the measuring technique is an optical measuring technique.
8. (Original) The method of claim 1 wherein the measuring step and the forming step are performed using processing modules of a single substrate processing system.

RESPONSE TO FINAL OFFICE ACTION**S/N 10/666,317****Page 3 of 10**

9. (Original) The method of claim 1 wherein the adjusting step comprises calculating an adjustment for the process recipe of the etch process.
10. (Original) The method of claim 9 wherein the adjustment is an adjustment for at least one parameter related to a thickness of a film of the material removed from sidewalls of the structures during the etch process.
11. (Original) The method of claim 10 wherein the at least one parameter is selected from a group consisting of a duration of time for overetching the structures, a flow rate and/or pressure of an etchant gas or gases, a plasma source power, a substrate bias power, a material of the structures and a thickness of sidewalls of the structures.
12. (Previously Presented) A method for controlling dimensions a gate structure of a field effect transistor formed on a substrate using an etch process, comprising:
providing the substrate having a patterned etch mask formed upon a film stack of the gate structure;
measuring dimensions of elements of the mask on the substrate;
adjusting a process recipe for an overetch step of the etch process of etching a layer of the film stack using results of measuring the dimensions; and
forming structures in the layer by performing the etch process that uses the adjusted process recipe.
13. (Original) The method of claim 12 wherein the layer is selected from a group consisting of a gate conductor layer, a gate electrode layer, and a gate dielectric layer.
14. (Previously Presented) The method of claim 13 wherein the gate conductor layer comprises WSi, the gate electrode layer comprises doped polysilicon and the gate dielectric layer comprises SiO₂ or HfO₂.

RESPONSE TO FINAL OFFICE ACTION**S/N 10/686,317****Page 4 of 10**

15. (Original) The method of claim 12 wherein the mask is a patterned hard etch mask or a patterned photoresist mask.
16. (Original) The method of claim 12 wherein the mask comprises a material selected from a group consisting of SiON, SiO₂, Si₃N₄, HfO₂ and α -carbon.
17. (Original) The method of claim 12 wherein the dimensions are smallest widths of the elements.
18. (Original) The method of claim 12 wherein the dimensions are measured using a non-destructive measuring technique.
19. (Original) The method of claim 18 wherein the measuring technique is an optical measuring technique.
20. (Original) The method of claim 12 wherein the measuring step and the forming step are performed using processing modules of a single substrate processing system.
21. (Original) The method of claim 12 wherein the adjusting step comprises calculating an adjustment for the process recipe of the etch process for etching the layer.
22. (Previously Presented) The method of claim 21 wherein the adjustment is an adjustment for at least one parameter related to a thickness of a film of material removed from sidewalls of the layer during the etch process.
23. (Original) The method of claim 22 wherein the at least one parameter is selected from a group consisting of a duration of time for overetching the structures, a flow rate and/or pressure of an etchant gas or gases, a plasma source power, a substrate bias power, a material of the structures and a thickness of sidewalls of the structures.

RESPONSE TO FINAL OFFICE ACTION
S/N 10/666,317
Page 5 of 10

24-28. (Cancelled)

29. (Previously Presented) The method of claim 1, wherein the measuring step further comprises measuring the dimensions of elements of the mask on the substrate in a number of regions.

30. (Previously Presented) The method of claim 29, wherein the measuring step further comprises measuring the dimensions of elements of the mask on the substrate in at least about five regions.

31. (Previously Presented) The method of claim 29, wherein the measuring step further comprises mathematically processing the measurements from the number of regions to create the result utilized in the adjusting step.

32. (Previously Presented) The method of claim 12, wherein the measuring step further comprises measuring the dimensions of elements of the mask on the substrate in a number of regions.

33. (Previously Presented) The method of claim 32, wherein the measuring step further comprises mathematically processing the measurements from the number of regions to create the result utilized in the adjusting step.